

A Rapid and Economical Method for Profiling Feature Heights during Microfabrication

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Electronic Supplementary Information

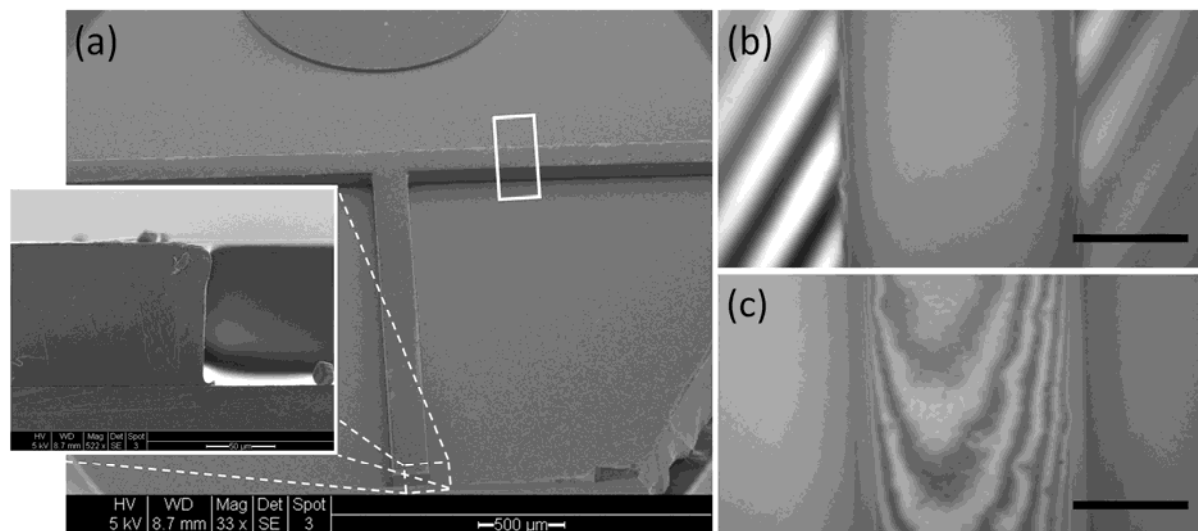


Fig. S1. Comparison between measurements of feature heights by (a) Scanning Electron Microscopy (SEM) and (b, c) interferometry. The solid white rectangle in (a) indicates the position of the interferometric measurement taken in (b) and (c). (b) shows the interference pattern from the silicon wafer and (c) shows the pattern from on top of the SU-8 layer. Scale bars in (b) and (c) correspond to 100 μm. The feature heights measured by SEM and interferometry were found to be $105.0 \pm 0.1 \mu\text{m}$ and $109.5 \pm 0.0 \mu\text{m}$ respectively.

Table S1. Summary of measurements ($n = 3$ for each height). S.D. = standard deviation of the measurements

Sample #	Height ($\mu\text{m} \pm \text{S.D.}$)	
	Interferometry	SEM
1	10 ± 0.0	10.6 ± 0.2
2	16.3 ± 0.2	16.3 ± 0.2
3	25.0 ± 0.2	25.3 ± 0.4
4	53.5 ± 0.4	52.4 ± 0.2
5	69.5 ± 0.5	67.6 ± 0.1
6	109.5 ± 0.0	105.0 ± 0.1
7	143.1 ± 0.4	140.6 ± 0.2

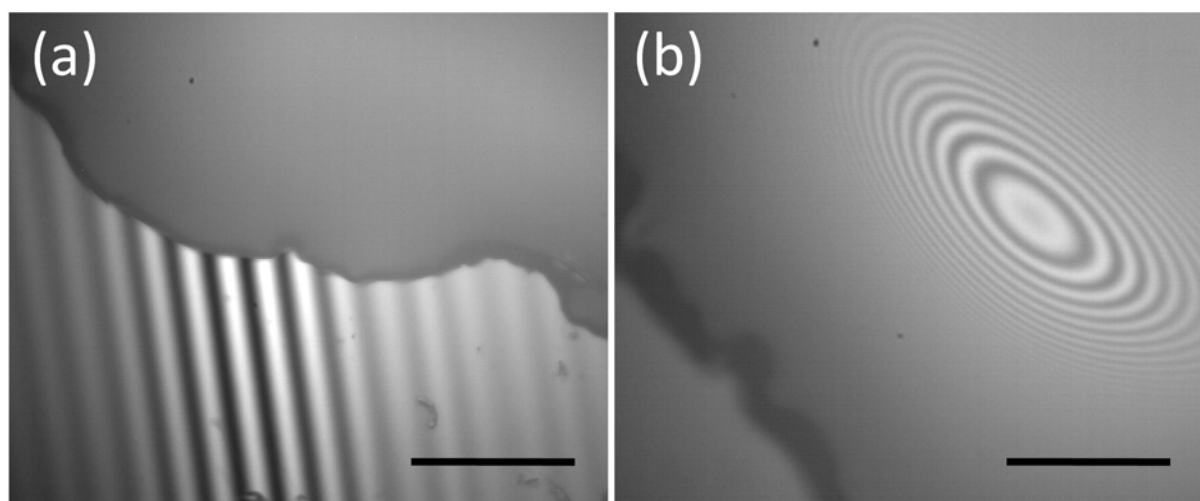


Fig. S2. Comparison of interference patterns on (a) the silicon wafer and (b) a 23 μm thick freshly spin coated, wet SU-8 layer. Scale bars correspond to 100 μm .